



## CRTE10DN06LD-G

**General Description:**

CRTE10DN06LD-G the silicon N-channel Enhanced VDMOSFETs, is obtained by the high density Trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is SOP-8L, which accords with the Halogen Free standard.

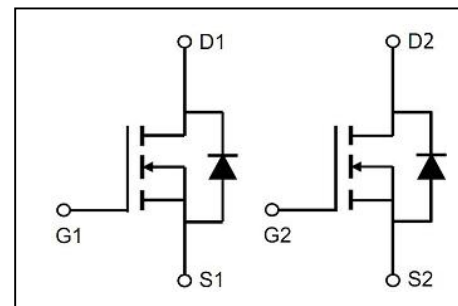
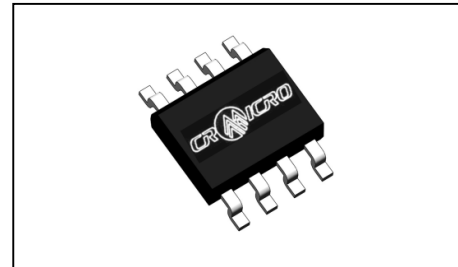
**Features:**

- l Fast Switching
- l Low ON Resistance ( $R_{ds(on)} \leq 100m\Omega$ )
- l Low Gate Charge
- l Low Reverse transfer capacitances
- l 100% Single Pulse avalanche energy Test
- l Halogen Free

**Applications:**

Power switch circuit of adaptor and charger.

|                             |     |            |
|-----------------------------|-----|------------|
| $V_{DSS}$                   | 60  | V          |
| $I_D$                       | 3.3 | A          |
| $P_D(T_a=25^\circ\text{C})$ | 1.7 | W          |
| $R_{DS(ON)}$                | 75  | m $\Omega$ |



**Absolute** ( $T_A = 25^\circ\text{C}$  unless otherwise specified):

| Symbol         | Parameter                                          | Rating          | Units               |
|----------------|----------------------------------------------------|-----------------|---------------------|
| $V_{DSS}$      | Drain-to-Source Voltage                            | 60              | V                   |
| $I_D$          | Continuous Drain Current                           | 3.3             | A                   |
|                | Continuous Drain Current $T_A = 100^\circ\text{C}$ | 2.1             | A                   |
| $I_{DM}^{a1}$  | Pulsed Drain Current                               | 13.2            | A                   |
| $V_{GS}$       | Gate-to-Source Voltage                             | $\pm 20$        | V                   |
| $E_{AS}^{a2}$  | Single Pulse Avalanche Energy                      | 11.2            | mJ                  |
| $P_D$          | Power Dissipation                                  | 1.7             | W                   |
|                | Derating Factor above $25^\circ\text{C}$           | 0.014           | W/ $^\circ\text{C}$ |
| $T_J, T_{stg}$ | Operating Junction and Storage Temperature Range   | 150, -55 to 150 | $^\circ\text{C}$    |

**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$  unless otherwise specified):

| <b>OFF Characteristics</b> |                                   |                                                          |        |      |      |         |
|----------------------------|-----------------------------------|----------------------------------------------------------|--------|------|------|---------|
| Symbol                     | Parameter                         | Test Conditions                                          | Rating |      |      | Units   |
|                            |                                   |                                                          | Min.   | Typ. | Max. |         |
| $V_{DSS}$                  | Drain to Source Breakdown Voltage | $V_{GS}=0V, I_D=250\mu A$                                | 60     | --   | --   | V       |
| $I_{DSS}$                  | Drain to Source Leakage Current   | $V_{DS} = 60V, V_{GS}= 0V,$<br>$T_J = 25^\circ\text{C}$  | --     | --   | 1    | $\mu A$ |
|                            |                                   | $V_{DS} = 48V, V_{GS}= 0V,$<br>$T_J = 125^\circ\text{C}$ | --     | --   | 100  |         |
| $I_{GSS(F)}$               | Gate to Source Forward Leakage    | $V_{GS} = +20V$                                          | --     | --   | 100  | nA      |
| $I_{GSS(R)}$               | Gate to Source Reverse Leakage    | $V_{GS} = -20V$                                          | --     | --   | -100 | nA      |

| <b>ON Characteristics</b>                        |                               |                                   |        |      |      |           |
|--------------------------------------------------|-------------------------------|-----------------------------------|--------|------|------|-----------|
| Symbol                                           | Parameter                     | Test Conditions                   | Rating |      |      | Units     |
|                                                  |                               |                                   | Min.   | Typ. | Max. |           |
| $R_{DS(ON)}$                                     | Drain-to-Source On-Resistance | $V_{GS}=10V, I_D=3A$              | --     | 75   | 100  | $m\Omega$ |
|                                                  |                               | $V_{GS}=4.5V, I_D=2A$             | --     | 101  | 125  | $m\Omega$ |
| $V_{GS(TH)}$                                     | Gate Threshold Voltage        | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 0.8    | 1.3  | 2    | V         |
| Pulse width $t_p \leq 300\mu s, \delta \leq 2\%$ |                               |                                   |        |      |      |           |

| <b>Dynamic Characteristics</b> |                              |                                             |        |       |      |          |
|--------------------------------|------------------------------|---------------------------------------------|--------|-------|------|----------|
| Symbol                         | Parameter                    | Test Conditions                             | Rating |       |      | Units    |
|                                |                              |                                             | Min.   | Typ.  | Max. |          |
| $R_g$                          | Gate resistance              | $V_{GS}=0V, V_{DS}=0V, f=1MHz$              | --     | 2.9   | --   | $\Omega$ |
| $C_{iss}$                      | Input Capacitance            | $V_{GS} = 0V, V_{DS} = 30V$<br>$f = 1.0MHz$ | --     | 297.6 | --   | pF       |
| $C_{oss}$                      | Output Capacitance           |                                             | --     | 25.0  | --   |          |
| $C_{rss}$                      | Reverse Transfer Capacitance |                                             | --     | 17.2  | --   |          |

| <b>Resistive Switching Characteristics</b> |                                 |                                                   |        |      |      |       |
|--------------------------------------------|---------------------------------|---------------------------------------------------|--------|------|------|-------|
| Symbol                                     | Parameter                       | Test Conditions                                   | Rating |      |      | Units |
|                                            |                                 |                                                   | Min.   | Typ. | Max. |       |
| $t_{d(ON)}$                                | Turn-on Delay Time              | $V_{GS}=10V, R_G=2\Omega$<br>$V_{DD}=30V, I_D=3A$ | --     | 6.2  | --   | ns    |
| $t_r$                                      | Rise Time                       |                                                   | --     | 2.3  | --   |       |
| $t_{d(OFF)}$                               | Turn-Off Delay Time             |                                                   | --     | 15   | --   |       |
| $t_f$                                      | Fall Time                       |                                                   | --     | 2.1  | --   |       |
| $Q_{g(10V)}$                               | Total Gate Charge               | $I_D = 3A, V_{DD} = 30V$<br>$V_{GS} = 10V$        | --     | 6.8  | --   | nC    |
| $Q_{g(5V)}$                                | Total Gate Charge               |                                                   | 0.7    | 3.8  | 6.8  |       |
| $Q_{gs}$                                   | Gate to Source Charge           |                                                   | --     | 1.1  | --   |       |
| $Q_{gd}$                                   | Gate to Drain ("Miller") Charge |                                                   | --     | 1.8  | --   |       |

| Source-Drain Diode Characteristics                        |                                        |                                   |        |      |      |       |
|-----------------------------------------------------------|----------------------------------------|-----------------------------------|--------|------|------|-------|
| Symbol                                                    | Parameter                              | Test Conditions                   | Rating |      |      | Units |
|                                                           |                                        |                                   | Min.   | Typ. | Max. |       |
| $I_S$                                                     | Continuous Source Current (Body Diode) | $T_C = 25^\circ\text{C}$          | --     | --   | 3.3  | A     |
| $I_{SM}$                                                  | Maximum Pulsed Current (Body Diode)    |                                   | --     | --   | 13.2 | A     |
| $V_{SD}$                                                  | Diode Forward Voltage                  | $I_S=3\text{A}, V_{GS}=0\text{V}$ | --     | --   | 1.2  | V     |
| $t_{rr}$                                                  | Reverse Recovery Time                  | $di/dt=100\text{A}/\mu\text{s}$   | --     | 29.1 | --   | ns    |
| $Q_{rr}$                                                  | Reverse Recovery Charge                | $I_F=3\text{A}$                   | --     | 22.7 | --   | nC    |
| Pulse width $t_p \leq 300\mu\text{s}$ , $\delta \leq 2\%$ |                                        |                                   |        |      |      |       |

| Symbol          | Parameter           | Max. | Units                     |
|-----------------|---------------------|------|---------------------------|
| $R_{\theta JA}$ | Junction-to-Ambient | 70   | $^\circ\text{C}/\text{W}$ |

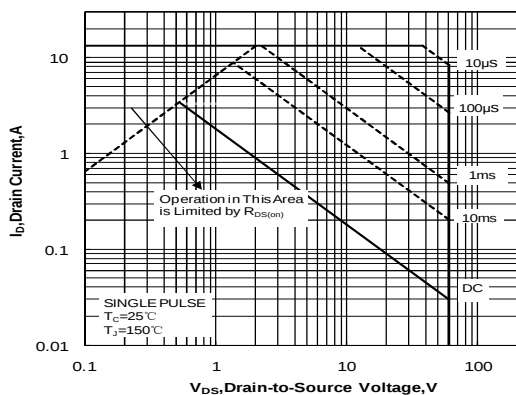
**Notes:**

<sup>a1</sup>: Repetitive rating; pulse width limited by maximum junction temperature

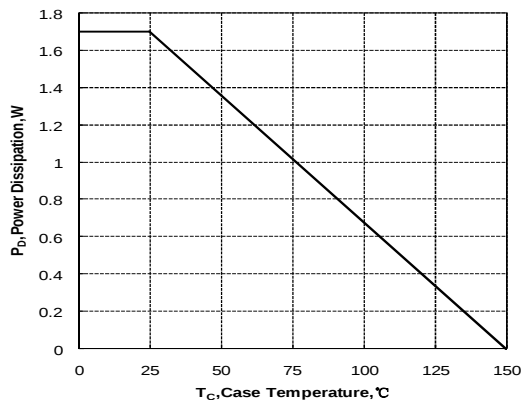
<sup>a2</sup>:  $L=0.5\text{mH}$ ,  $I_D=6.7\text{A}$ , Start  $T_J=25^\circ\text{C}$

<sup>a3</sup>: Recommend soldering temperature defined by IPC/JEDEC J-STD 020

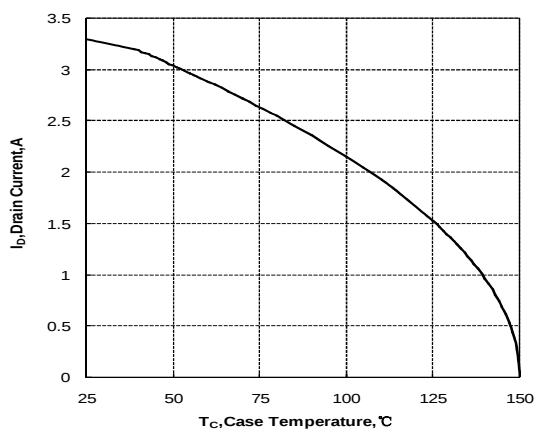
## Characteristics Curve:



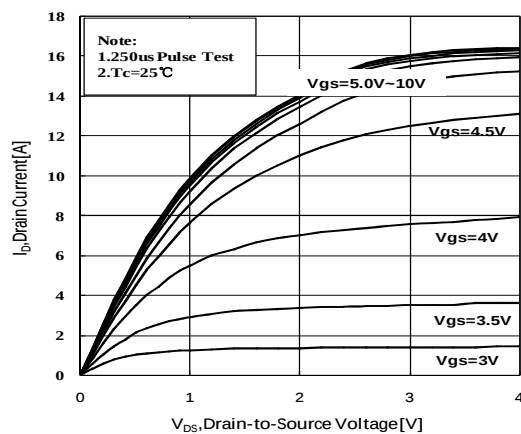
**Figure 1 . Maximum Safe Operating Area**



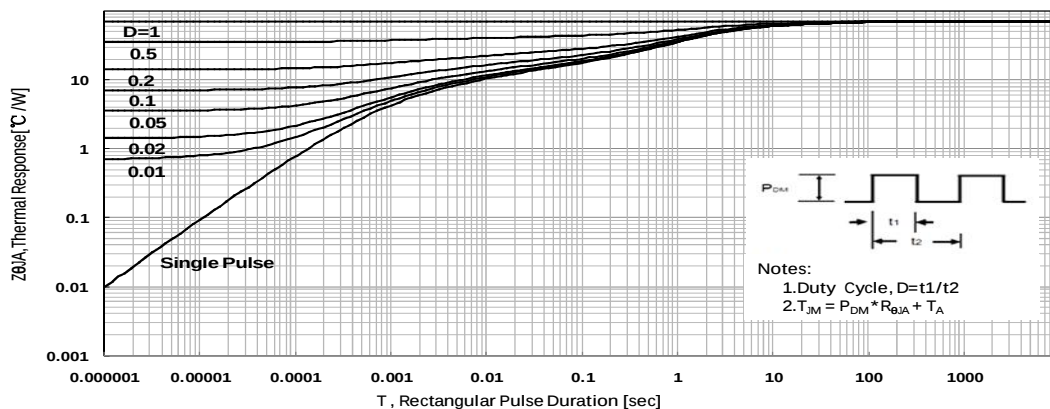
**Figure 2. Maximum Power Dissipation vs Case Temperature**



**Figure 3. Maximum Continuous Drain Current vs Case Temperature**



**Figure 4. Typical output Characteristics**



**Figure 5 Maximum Effective Thermal Impedance , Junction to Ambient**

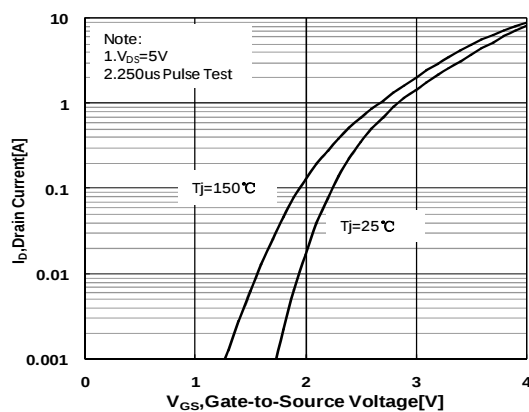


Figure 6 Typical Transfer Characteristics

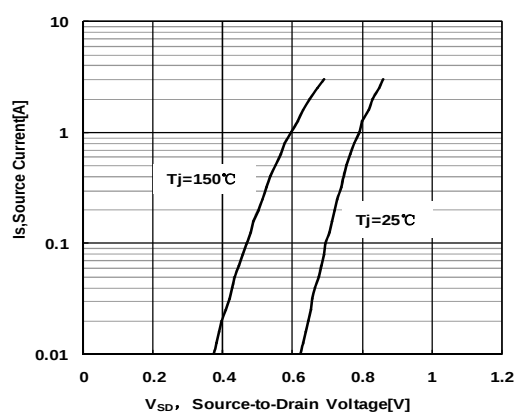


Figure 7 Typical Body Diode Transfer Characteristics

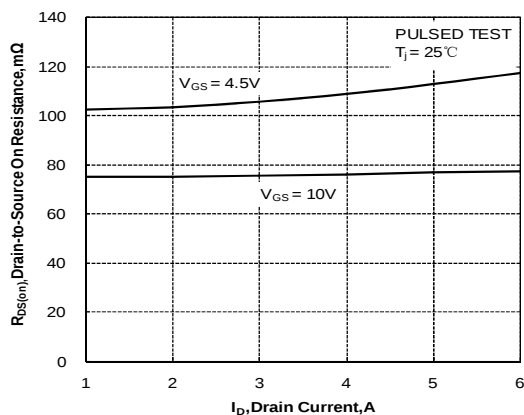


Figure 8. Drain-to-Source On Resistance vs Drain Current

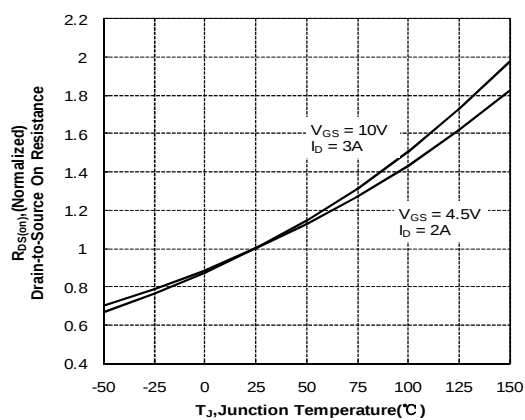


Figure 9. Normalized On Resistance vs Junction Temperature

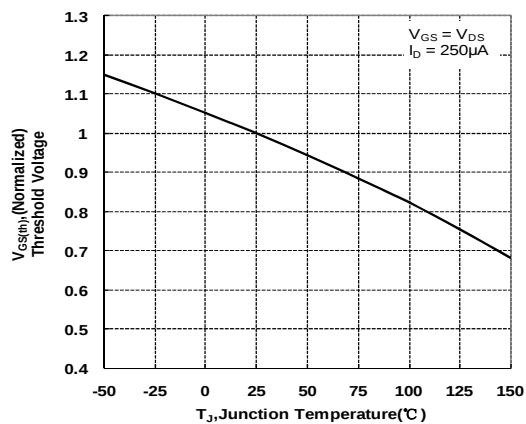


Figure10. Normalized Threshold Voltage vs Junction Temperature

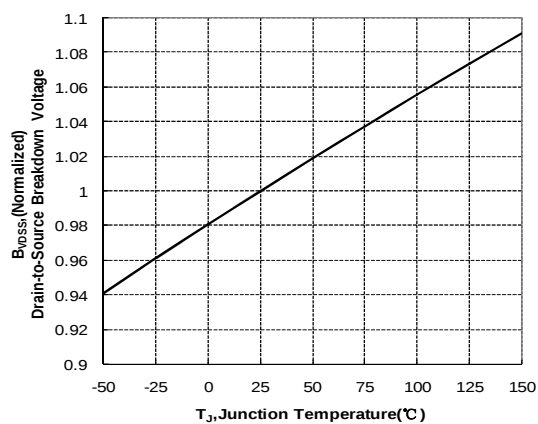
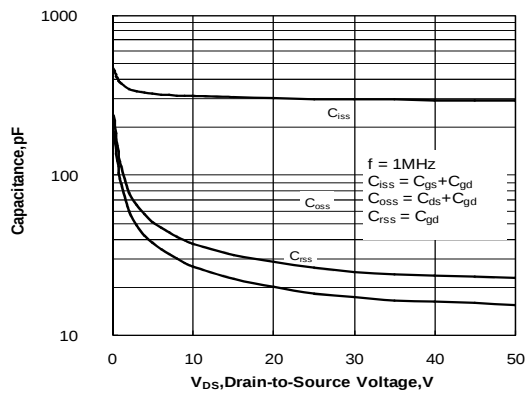
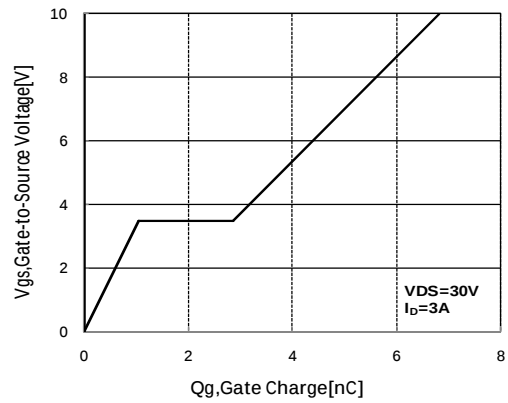


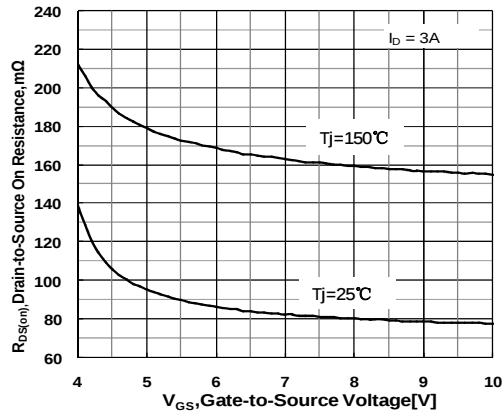
Figure 11. Normalized Breakdown Voltage vs Junction Temperature



**Figure 12. Capacitance Characteristics**



**Figure 13 Typical Gate Charge vs Gate to Source Voltage**



**Figure 14 Drain-to-Source On Resistance Gate-to-Source Voltage**

### Test Circuit and Waveform:

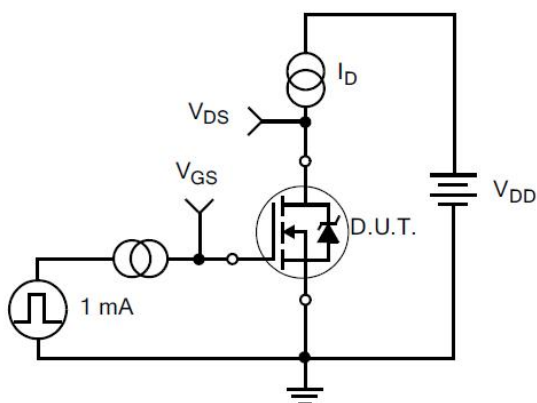


Figure 15. Gate Charge Test Circuit

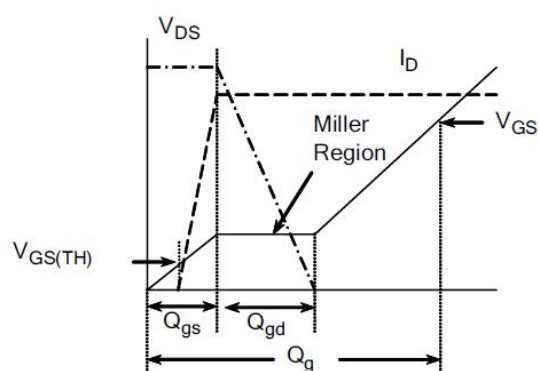


Figure 16. Gate Charge Waveforms

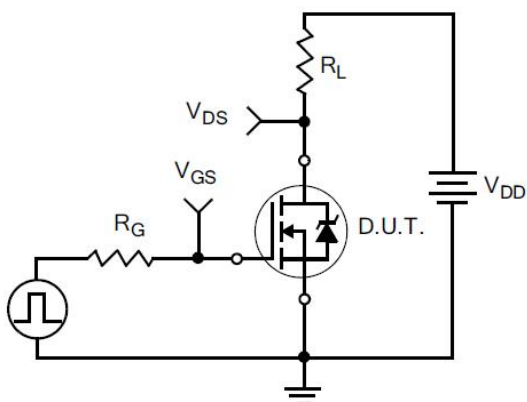


Figure 17. Resistive Switching Test Circuit

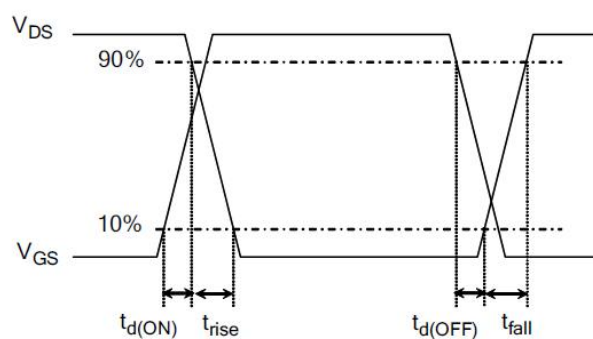


Figure 18. Resistive Switching Waveforms

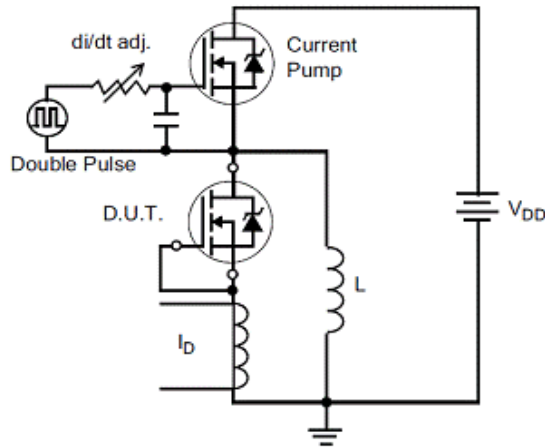


Figure 19. Diode Reverse Recovery Test Circuit

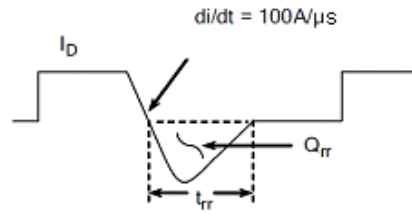


Figure 20. Diode Reverse Recovery Waveform

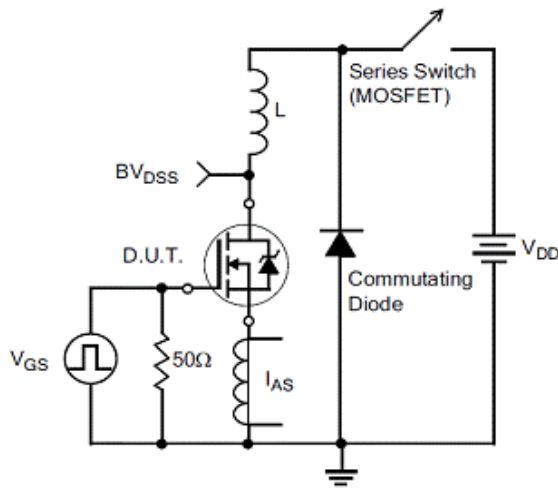


Figure 21. Unclamped Inductive Switching Test Circuit

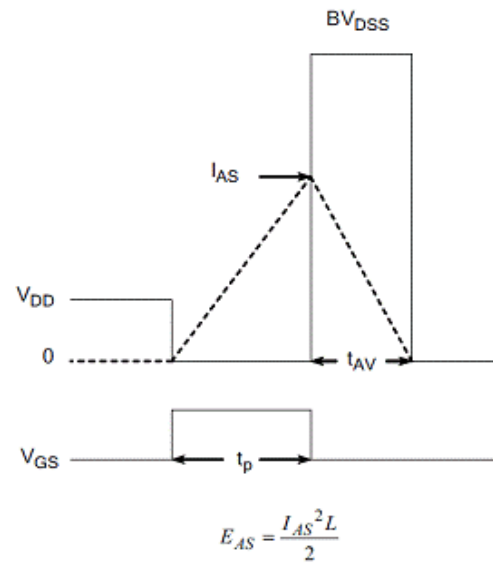
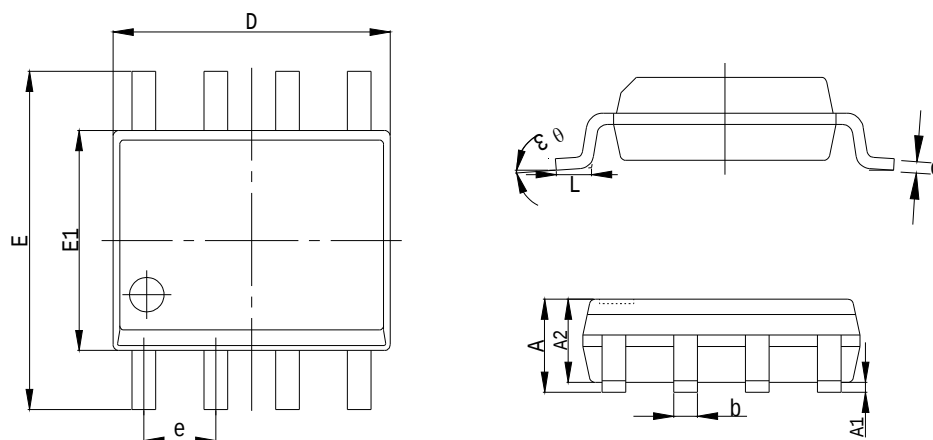


Figure 22. Unclamped Inductive Switching Waveform

**Package Information:**


| Items | Values(mm) |      |
|-------|------------|------|
|       | MIN        | MAX  |
| A     | 1.30       | 1.80 |
| A1    | 0.10       | 0.25 |
| A2    | 1.30       | 1.50 |
| E     | 5.80       | 6.20 |
| E1    | 3.80       | 4.00 |
| D     | 4.80       | 5.00 |
| L     | 0.40       | 0.90 |
| e     | 1.27TYP    |      |
| b     | 0.37       | 0.47 |
| c     | 0.20 TYP   |      |
| θ     | 0°         | 8°   |

**SOP-8L Package**

**The name and content of poisonous and harmful material in products**

| Part's Name   | Hazardous Substance                                                                                                                                                                                                                                                          |       |        |        |       |       |       |       |       |       |
|---------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------|--------|--------|-------|-------|-------|-------|-------|-------|
|               | Pb                                                                                                                                                                                                                                                                           | Hg    | Cd     | Cr(VI) | PBB   | PBDE  | DIBP  | DEHP  | DBP   | BBP   |
| Limit         | ≤0.1%                                                                                                                                                                                                                                                                        | ≤0.1% | ≤0.01% | ≤0.1%  | ≤0.1% | ≤0.1% | ≤0.1% | ≤0.1% | ≤0.1% | ≤0.1% |
| Lead Frame    | ○                                                                                                                                                                                                                                                                            | ○     | ○      | ○      | ○     | ○     | ○     | ○     | ○     | ○     |
| Molding       | ○                                                                                                                                                                                                                                                                            | ○     | ○      | ○      | ○     | ○     | ○     | ○     | ○     | ○     |
| Chip          | ○                                                                                                                                                                                                                                                                            | ○     | ○      | ○      | ○     | ○     | ○     | ○     | ○     | ○     |
| Wire Bonding  | ○                                                                                                                                                                                                                                                                            | ○     | ○      | ○      | ○     | ○     | ○     | ○     | ○     | ○     |
| Electric glue | ○                                                                                                                                                                                                                                                                            | ○     | ○      | ○      | ○     | ○     | ○     | ○     | ○     | ○     |
| Note          | <p>○: Means the hazardous material is under the criterion of 2011/65/EU.</p> <p>×: Means the hazardous material exceeds the criterion of 2011/65/EU.</p> <p>The plumbum element of solder exist in products presently, but within the allowed range of Eurogroup's RoHS.</p> |       |        |        |       |       |       |       |       |       |

**Warnings**

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. It is suggested to be used under 80 percent of the maximum ratings of the device.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. VDMOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. This publication is made by Huajing Microelectronics and subject to regular change without notice.

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